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a MOS transistor of a second type directly connected between the second supply terminal and the gate of the transistor of the first type by its source and its drain, respectively; and
a capacitor having a first terminal directly connected to the first supply terminal and a second terminal directly connected to the gate of the transistor of the second type.

2. (Amended) The protection device according to claim 1, wherein a resistor interconnects the gate and the source of [each of] the MOS transistor[s] of the first [and second] type.

☐ Please add the following claims:

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~~27~~. The protection device according to claim 1, wherein a resistor interconnects the gate and the source of the MOS transistor of the second type.

11
~~28~~. A protection device according to claim 1, wherein the transistor of the second type has a faster turn-on rate than the transistor of the first type.

12
~~29~~. A protection device according to claim 1, wherein the transistor of the second type has a smaller capacitance than the transistor of the first type.

13
~~30~~. A protection device according to claim 1, wherein the transistor of the second type has a smaller W/L ratio than the transistor of the first type.

6 *7*
~~31~~. A protection device according to claim ~~27~~ *7*, further comprising a reverse connected diode between the gate and the source of the transistor of the second type and wherein the transistor of the second type has a faster turn-on rate than the transistor of the first type.

9 *7*
~~32~~. A protection device according to claim ~~27~~ *7*, further comprising a reverse connected diode between the gate and the source of the transistor of the second type and wherein the transistor of the second type has a smaller capacitance than the transistor of the first type.

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33. A protection device according to claim 27, further comprising a reverse connected diode between the gate and the source of the transistor of the second type and wherein the transistor of the second type has a smaller W/L ratio than the transistor of the first type.

22 14
34. The device of the claim 18, wherein the first means for switching has a faster turn-on rate than the second means for switching.

23 10
35. The device of claim 18, wherein the first means for switching has a smaller capacitance than the second means for switching.

24 14
36. The device of claim 18, wherein the first means for switching has a smaller W/L ratio than the second means for switching.

19 18
37. The device of claim 22, wherein the transistor of the first type has a faster turn-on rate than the transistor of the second type.

20 14
38. The device of claim 22, wherein the transistor of the first type has a smaller capacitance than the transistor of the second type.

21 18
39. The device of claim 22, wherein the transistor of the first type has a smaller W/L ratio than the transistor of the second type.

REMARKS

In response to the Office Action mailed on April 29, 1998, Applicant respectfully requests reconsideration. To further the prosecution of this application, Applicant has amended the claims and submitted the following remarks.

Claims 7-13, 15, 17, 23 and 25 have been canceled. Claims 1 and 2 have been amended herein. Dependent claims 27-39 have been added. Claims 1-6, 18-22 and 27-39 now remain in this application of which claims 1 and 18 are independent.

14